



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

TO-92 Plastic-Encapsulate Transistors

PCR 0.6 A Silicon Planar pnpn Thyristor

FEATURES

Current- I_{GT} : 120 μ A

I_{TRMS} : 0.6A

V_{DRM} : 400V

TO—92

1.CATHODE

2.GATE

3.ANODE



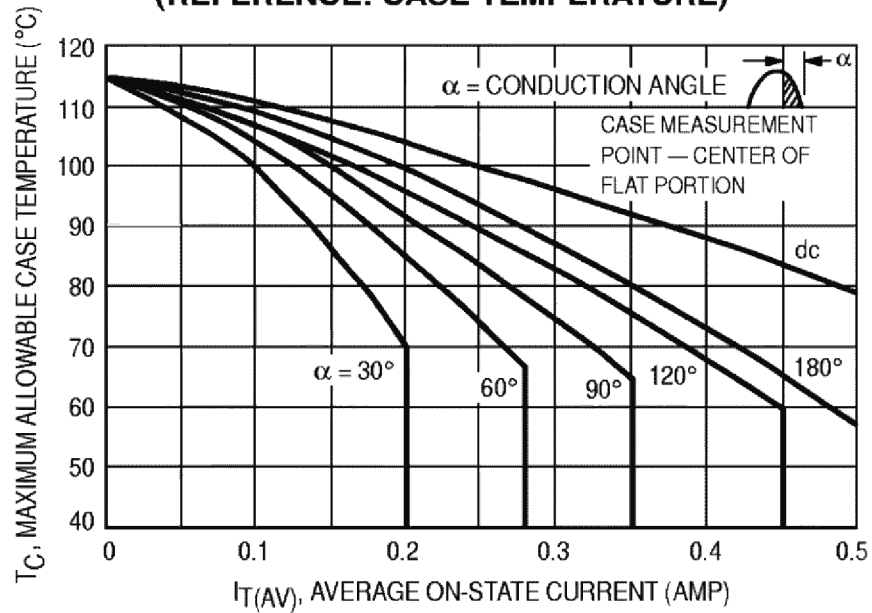
Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

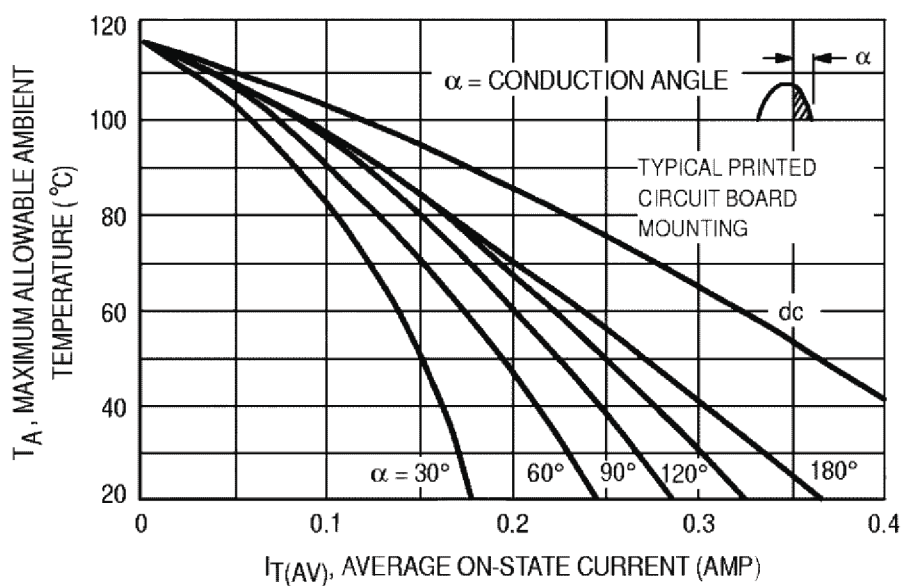
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
On state voltage	V_{TM}	$I_{TM}=0.6A$		1.7	V
Gate trigger voltage	V_{GTF}	$V_{AK}=7V$		0.8	V
Repetitive peak off-state voltage	V_{DRM}	$I_{DRM}=10\ \mu A$	400		V
Holding current	I_H	$I_{HL}=20\ mA, A_v=7\ V$		5	mA
Gate trigger current	I_{GTF}	$V_{AR}=7V$	5	15	μA
			15	30	μA
			30	45	μA
			45	60	μA
			60	80	μA
			80	120	μA

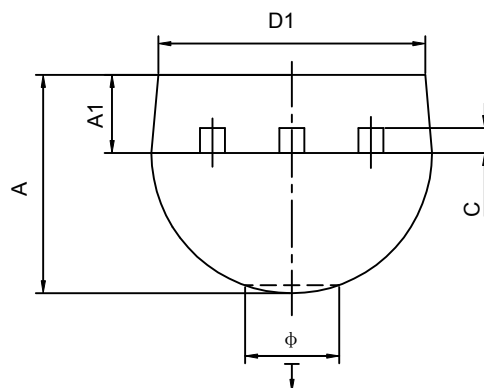
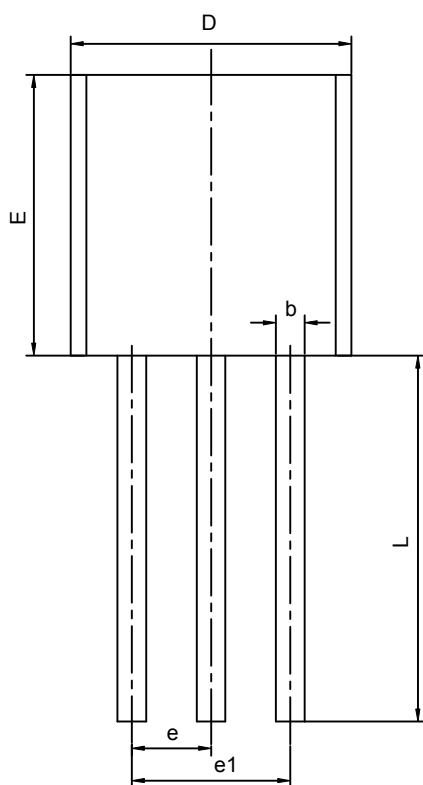
**FIGURE 1 – MCR100-8 CURRENT DERATING
(REFERENCE: CASE TEMPERATURE)**



**FIGURE 2 – MCR100-8 CURRENT DERATING
(REFERENCE: AMBIENT TEMPERATURE)**



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
$\downarrow$	0.000	0.380	0.000	0.015